

### 20V P-Channel Enhancement Mode MOSFET

-20 V Current -500mA

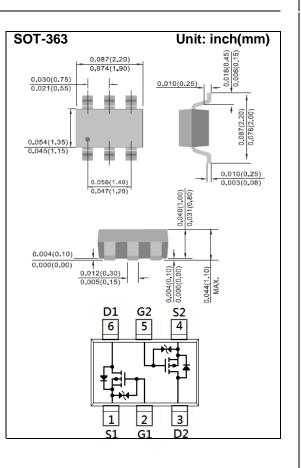
#### Features

Voltage

- Low Voltage Drive (1.2V).
- Advanced Trench Process Technology
- Specially Designed for Load switch, PWM Application, etc.
- ESD Protected
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

#### **Mechanical Data**

- Case: SOT-363 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0002 ounces, 0.006 grams
- Marking: T07



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER   |                      | SYMBOL                           | LIMIT       | UNITS |
|---|----------------------|----------------------------------|-------------|-------|
| Drain-Source Voltage  |                      | V <sub>DS</sub>                  | -20         | V     |
| Gate-Source Voltage   |                      | V <sub>GS</sub>                  | <u>+</u> 10 | V     |
| Continuous Drain Current  |                      | I <sub>D</sub>                   | -500        | mA    |
| Pulsed Drain Current (Note 4)   |                      | I <sub>DM</sub>                  | -1000       | mA    |
| Power Dissipation   | T <sub>a</sub> =25°C | P <sub>D</sub>                   | 350         | mW    |
|   | Derate above 25°C    |                                  | 2.8         | mW/°C |
| Operating Junction and Storage Temperature Range                        |                      | T <sub>J</sub> ,T <sub>STG</sub> | -55~150     | °C    |
| Typical Thermal resistance<br>- Junction to Ambient <sup>(Note 3)</sup> |                      | R <sub>θJA</sub>                 | 357         | °C/W  |





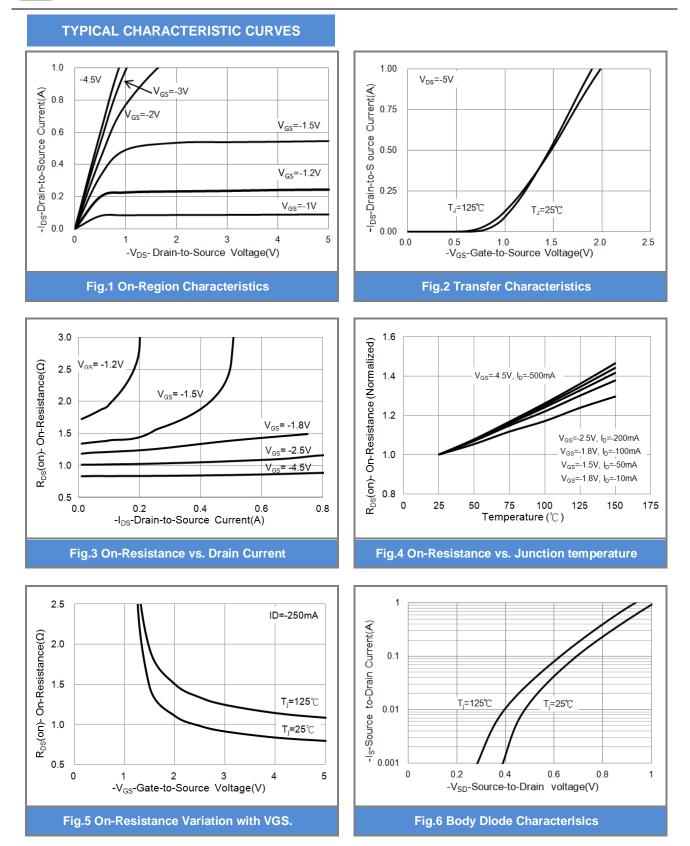
## **Electrical Characteristics** (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

| PARAMETER  | SYMBOL              | TEST CONDITION   | MIN. | TYP.       | MAX.        | UNITS |
|--|---------------------|--|------|------------|-------------|-------|
| Static   |                     |  |      |            |             |       |
| Drain-Source Breakdown Voltage                           | $BV_{DSS}$          | V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA  | -20  | -          | -           | V     |
| Gate Threshold Voltage                                   | V <sub>GS(th)</sub> | $V_{DS}=V_{GS}$ , $I_{D}=-250$ uA  | -0.3 | -0.59      | -1.0        | V     |
| Drain-Source On-State Resistance                         | R <sub>DS(on)</sub> | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-500mA   | -    | 0.85       | 1.2         | Ω     |
|  |                     | V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-200mA   | -    | 0.99       | 1.5         |       |
|  |                     | V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-100mA   | -    | 1.16       | 2.2         |       |
|  |                     | V <sub>GS</sub> =-1.5V, I <sub>D</sub> =-50mA  | -    | 1.33       | 3.6         |       |
|  |                     | V <sub>GS</sub> =-1.2V, I <sub>D</sub> =-10mA  | -    | 1.5        | 6.0         |       |
| Zero Gate Voltage Drain Current                          | I <sub>DSS</sub>    | V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V   | -    | -          | -1          | uA    |
| Gate-Source Leakage Current                              | I <sub>GSS</sub>    | V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V   | -    | <u>+</u> 2 | <u>+</u> 10 | uA    |
| Dynamic (Note 5)   |                     |  |      |            |             |       |
| Total Gate Charge  | $Q_g$               | - V <sub>DS</sub> =-10V, I <sub>D</sub> =-500mA,<br>- V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup> | -    | 1.4        | -           | nC    |
| Gate-Source Charge                                       | $Q_gs$              |  | -    | 0.19       | -           |       |
| Gate-Drain Charge  | $Q_gd$              |  | -    | 0.2        | -           |       |
| Input Capacitance  | Ciss                | $V_{DS}$ =-10V, $V_{GS}$ =0V,  | -    | 38         | -           | pF    |
| Output Capacitance                                       | Coss                |  | -    | 15         | -           |       |
| Reverse Transfer Capacitance                             | Crss                | f=1.0MHZ   | -    | 9          | -           |       |
| Turn-On Delay Time                                       | td <sub>(on)</sub>  |  | -    | 7.2        | -           | ns    |
| Turn-On Rise Time  | tr                  | $V_{DD}$ =-10V, $I_{D}$ =-500mA,<br>$V_{GS}$ =-4.5V,<br>$R_{G}$ =6 $\Omega^{(Note 1,2)}$           | -    | 21         | -           |       |
| Turn-Off Delay Time                                      | td <sub>(off)</sub> |  | -    | 85         | -           |       |
| Turn-Off Fall Time                                       | tf                  | R <sub>G</sub> =017  | -    | 116        | -           |       |
| Drain-Source Diode                                       |                     |  |      |            |             |       |
| Maximum Continuous Drain-Source<br>Diode Forward Current | I <sub>S</sub>      |  | -    | -          | -500        | mA    |
| Diode Forward Voltage                                    | V <sub>SD</sub>     | I <sub>S</sub> =-500mA, V <sub>GS</sub> =0V  | -    | -0.93      | -1.3        | V     |

NOTES :

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.







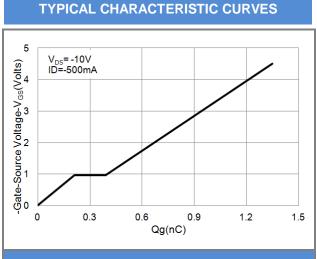


Fig.7 Gate-Charge Characteristics

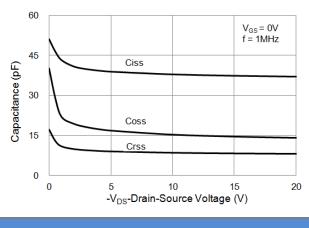
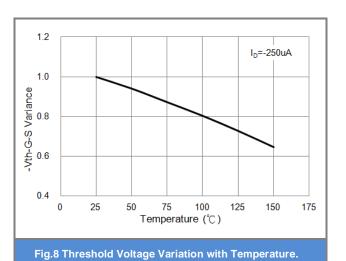


Fig.9 Capacitance vs. Drain-Source Voltage.





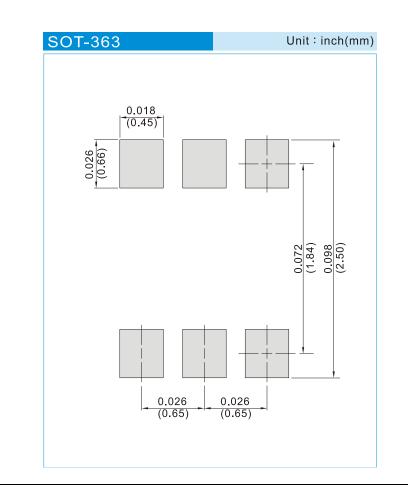




### PART NO PACKING CODE VERSION

| Part No Packing Code | Package Type | Packing type       | Marking | Version      |
|----------------------|--------------|--------------------|---------|--------------|
| PJT7807_R1_00001     | SOT-363      | 3K pcs / 7" reel   | T07     | Halogen free |
| PJT7807_R2_00001     | SOT-363      | 10K pcs / 13" reel | T07     | Halogen free |

### MOUNTING PAD LAYOUT







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